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978-1-107-41016-9 - Materials Research Society Symposium Proceedings: Volume 182:

Polysilicon Thin Films and Interfaces

Editors: Theodore Kamins, Bruha Raicu and Carl V. Thompson

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MATERIALS RESEARCH SOCIETY SYMPOSIUM PROCEEDINGS VOLUME 182

Polysilicon Thin Films and Interfaces

Symposium held April 17-19, 1990, San Francisco, California, U.S.A.

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MATERIALS RESEARCH SOCIETY

Pittsburgh, Pennsylvania

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Cambridge, New York, Melbourne, Madrid, Cape Town,
Singapore, São Paulo, Delhi, Mexico City

Cambridge University Press

32 Avenue of the Americas, New York NY 10013-2473, USA

Published in the United States of America by Cambridge University Press, New York

www.cambridge.org

Information on this title: www.cambridge.org/9781107410169

Materials Research Society

506 Keystone Drive, Warrendale, PA 15086

<http://www.mrs.org>

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First published 1990

First paperback edition 2012

Single article reprints from this publication are available through
University Microfilms Inc., 300 North Zeeb Road, Ann Arbor, MI 48106

CODEN: MRSPDH

ISBN 978-1-107-41016-9 Paperback

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Preface

The second symposium on polysilicon films and interfaces was held at the Spring 1990 Meeting of the Materials Research Society in San Francisco in April 1990. It continued the theme introduced in the first symposium held in 1987. This proceedings volume contains the majority of the papers presented at the symposium.

The papers covered a broad range of topics from deposition to electronic applications and even to the emerging field of microsensors and microactuators.

The organizers of the symposium wish to thank the speakers for their efforts in presenting the results of their research both in oral and written form. The following session chairmen contributed significantly to the success of the symposium by stimulating lively interchange of ideas: I. Calder, A. Chiang, M. Hammond, M. Hatalis, H. Kabza, J. Mayer, S. Murarka, R. Reif, and C. Wong. Our special thanks also go to the anonymous reviewers who guided us in the selection of papers.

Theodore Kamins
Bruha Raicu
Carl Thompson

September 1, 1990

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Acknowledgments

Financial support for the Symposium was provided by

AG Associates
Advanced Micro Devices, Inc.
Applied Materials
Lam Research Corp.
MEMC Electronic Material, Inc.
Northern Telecom Electronics
Peak Systems, Inc.
Prometrix
Varian Associates

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